

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Wang et al.

Appl. No.: 08/481,146

Filed: June 7, 1995

For: System and Method for Retiring Instructions in a Superscalar

Microprocessor

Art Unit: 2315

Examiner V Vi

Atty Docket: SP038.C1

Declaration Under 37 C.F.R. § 1.132

Assistant Commissioner for Patents Washington, DC 20231

Johannes Wang, Sanjiv Garg and Trevor A. Deosaran, Applicants in the identified patent application, declare and state as follows:

- We are the sole inventors of the subject matter described and claimed in part in the present application.
- 2. Le Trong Nguyen, Derek J. Lentz, Yoshiyuki Miyayama, Yasuaki Hagiwara, Te-Li Lau, Sze-Shun Wang and Quang H. Trang (co-inventors of U.S. Patent No. 5,560,032 to Nguyen et al.) were a part of S-MOS System's "Seabird" architecture project team. U.S. Patent No. 5,560,032 (the '032 patent) describes and claims in part a superscalar processing system having a plurality of stages, including a decoding and issuing stage and an execution stage. This superscalar processing system design resulted from the "Seabird" architecture project.
- 3. To the extent that the '032 patent discloses the details of the Instruction Retirement Unit (IRU), it is based upon the original work of Johannes Wang and Sanjiv Garg. Johannes Wang and Sanjiv Garg were also a part of S-MOS System's "Seabird" architecture project team.

- To the extent that the present application discloses additional details and features
 of the IRU, it is based upon the work of Johannes Wang, Sanjiv Garg and Trevor Deosaran.
- 5. The subject matter of the '032 patent that is relied upon by the Examiner in the outstanding 35 U.S.C. § 102(e) rejection is a description of the IRU that is further described and claimed in part in the present application.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Ву:		Date:
Johan	nes Wang	
By: Sanjiv	Garg	Date: 4 1 97
Ву:	·	Date:
Trevo	r A. Deosaran	